

Session TT

Transistor Power Amplifiers II

Chairman:

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This session encompasses a broad range of power amplifiers, from 950 MHz to 40 GHz, using a variety of device technologies: FET, HFET, PHEMT, and HBT.

The first two papers describe low-voltage amplifiers for use in 950 MHz and 1.9 GHz personal communications applications. The third paper employs a PHEMT, long the province of mm-wave amplifiers, at C-band to achieve high efficiency. The fourth paper achieves high efficiency over the 6 to 10 GHz band using an HBT MMIC. An x-band, 1 watt GaInP/GaAs HBT is reported in the fifth paper. The final paper of the session presents a 40 GHz HFET with a novel gate structure, promising high reliability.



3:30 p.m.–5:00 p.m., Thursday, June 17, 1993
Room 216/217

